## Photomultiplication-type Photodiode with Nanowire-embedded Polymer Matrix

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Photomultiplication—type organic photodiode with a nanowire (NW)—embedded polymer matrix is suggested to achieve prolonged trap lifetime and enhanced major carrier mobility. Growth of well—defined NWs with low structural defects within poly (3–hexylthiophene–2,5–diyl):[6,6]—phenyl— $C_{71}$ —butyricacid—methylester(100:1 w/w) bulk—heterojunction (BHJ) active layer is achieved with cyclohexanoe as a anit—solvent, which is analized by UV–Vis absorption spectroscopy, atomic force microscopy, transmission electron microscopy and grazing incidence X–ray diffraction analyses. Because of NW–embedding, remarkable increase of external quantum efficiency up to 250,000%, responsivity up to 1,300 A W<sup>-1</sup> and high specific detectivity up to 6.3×10<sup>13</sup> Jones can be realized by embedding an optimal amount of NW into conventional PM–OPD structured as ITO/PEDOT:PSS/BHJ/Al.